CRMKGH0814A

N-Channel 85V, 15mΩ Typ. Power MOSFET

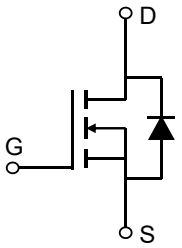
Description

Features

- 85V, 32A

  $R_{DS(ON)}$ Typ = 15mΩ @ V_{GS} = 10V

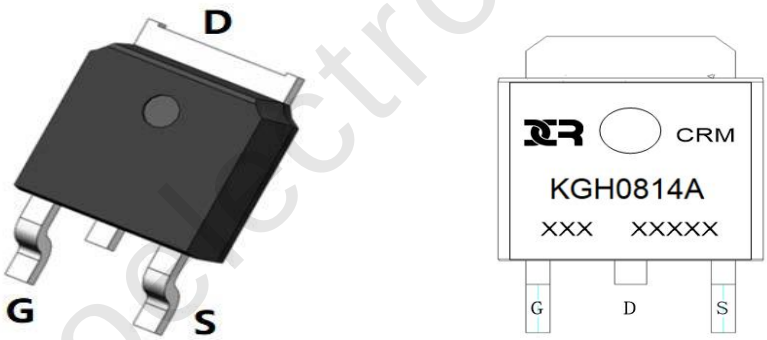
  Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMKGH0814A	CRMKGH0814A	TO-252-3L	TAPING	13"	2500	25000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		85	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	32	A
		T_C = 100°C	19.2	A
I_{DM}	Pulsed Drain Current (1)		128	A
E_{AS}	Single Pulsed Avalanche Energy (2)		36	mJ
P_D	Power Dissipation	T_C = 25°C	42	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	85	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 85V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.4	3	3.6	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 20A	-	15	19.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 40V, f = 1MHz	-	576	-	pF
C_{oss}	Output Capacitance		-	197	-	pF
C_{rss}	Reverse Transfer Capacitance		-	10	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 40V, I_D = 10A	-	25	-	nC
Q_{gs}	Gate Source Charge		-	8	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 40V I_D= 10A, R_{GEN} = 3Ω	-	12	-	ns
t_r	Turn-On Rise Time		-	8	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	20	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	32	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	128	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 10A, di/dt = 100A/us	-	33	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	45	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=40V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=12A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

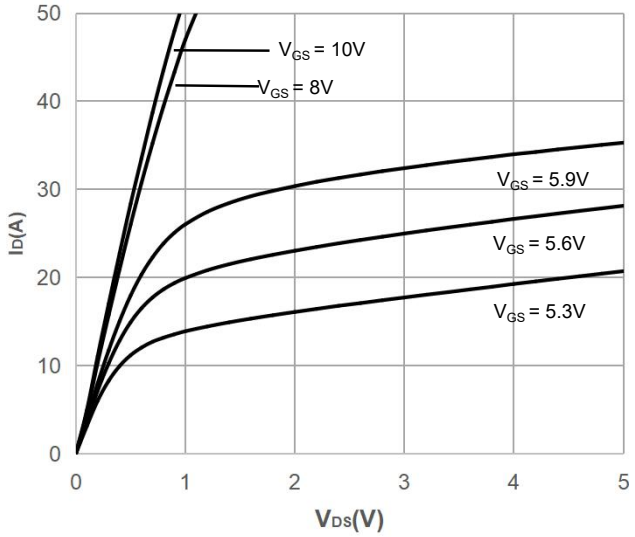


Figure 2: Typical Transfer Characteristics

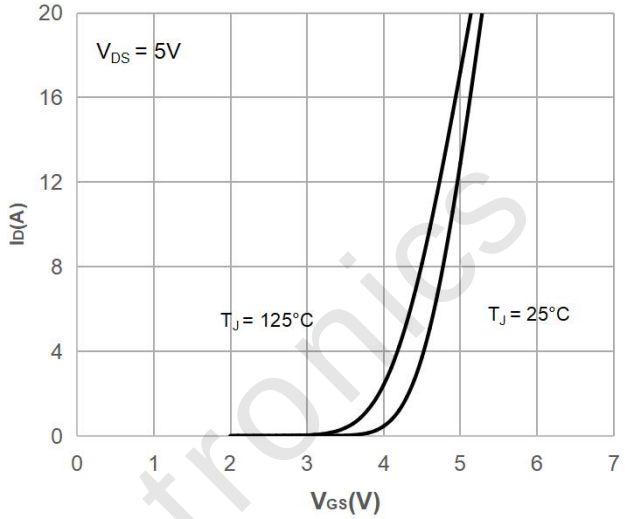


Figure 3: On-resistance vs. Drain Current

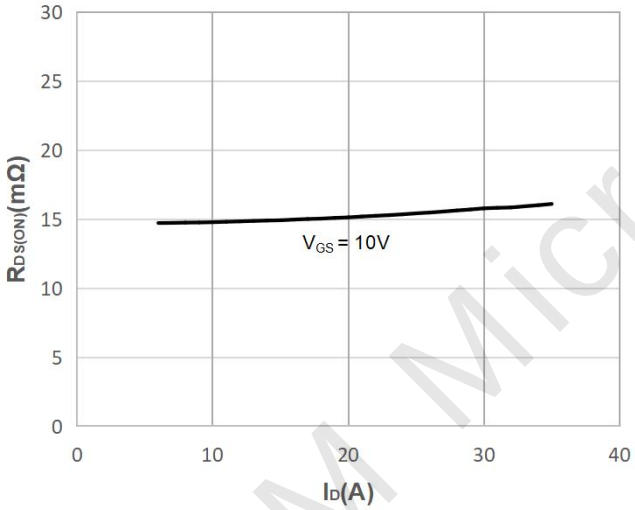


Figure 4: Body Diode Characteristics

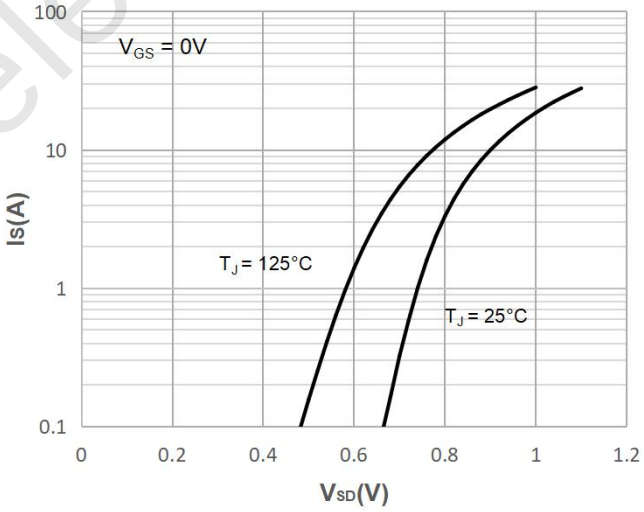


Figure 5: Gate Charge Characteristics

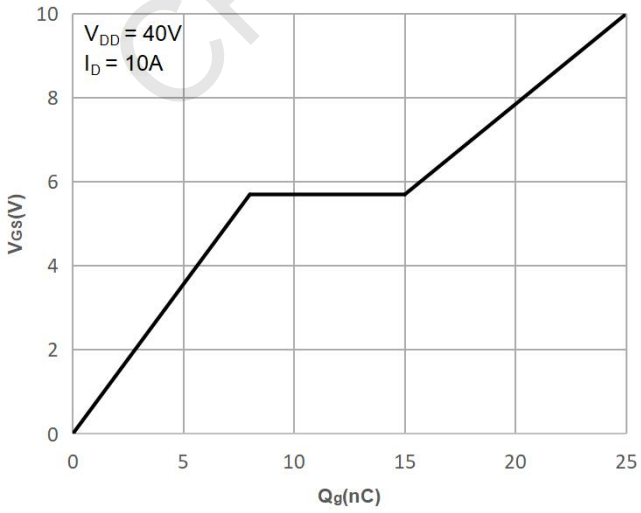
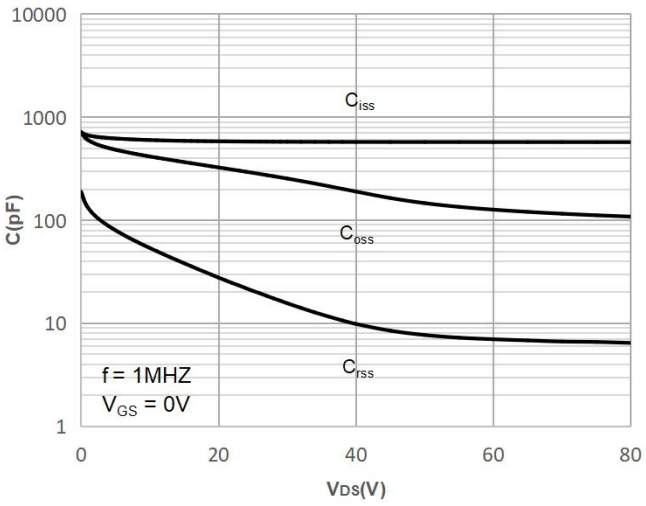


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

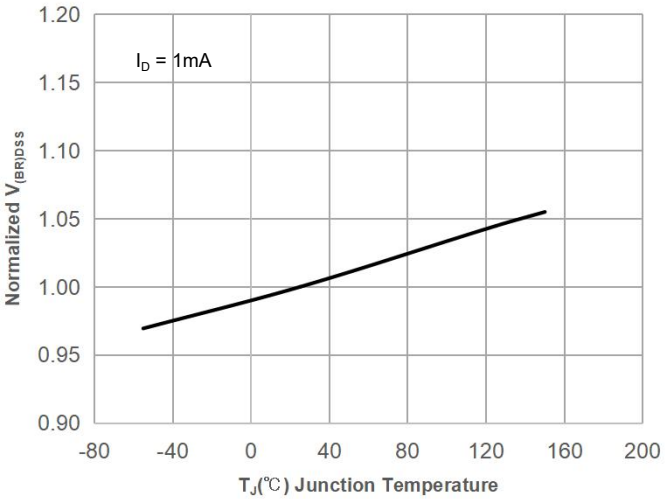


Figure 8: Normalized on Resistance vs. Junction Temperature

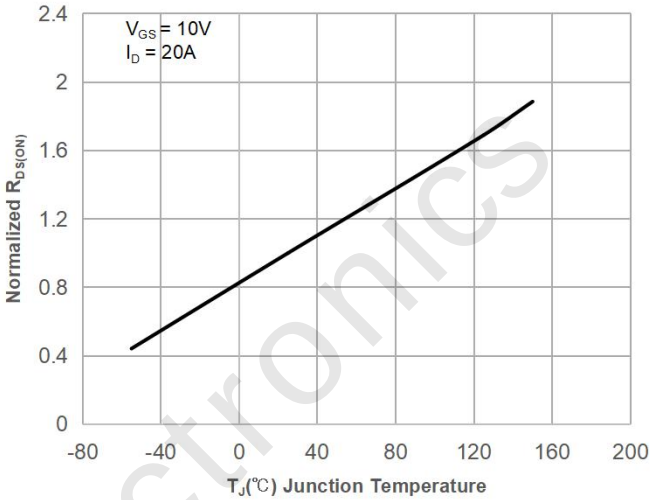


Figure 9: Maximum Safe Operating Area

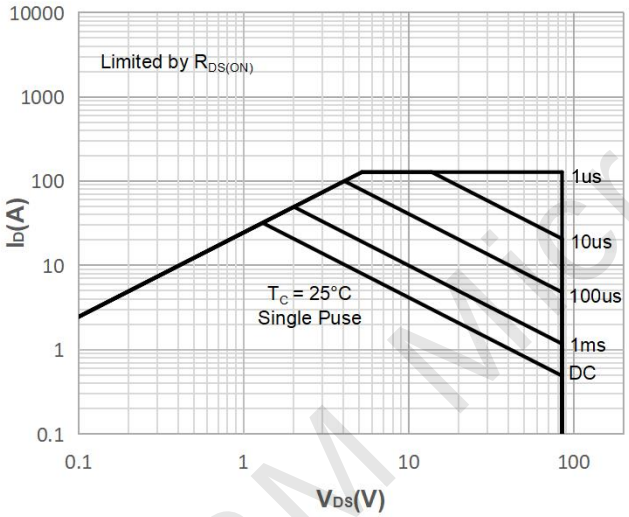


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

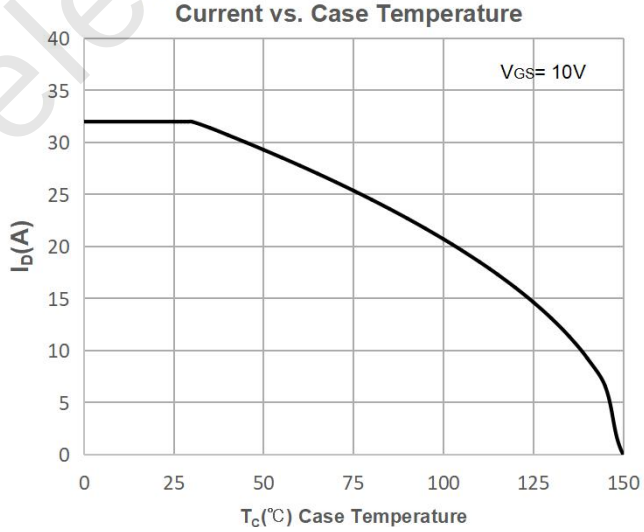


Figure 11: Normalized Maximum Transient Thermal Impedance

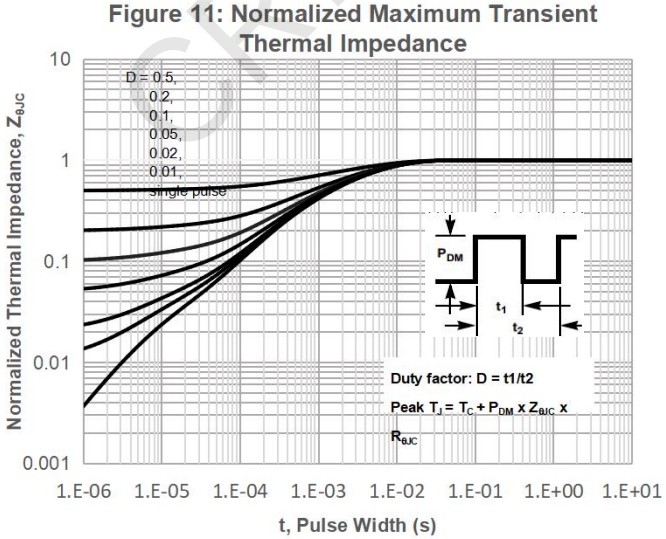
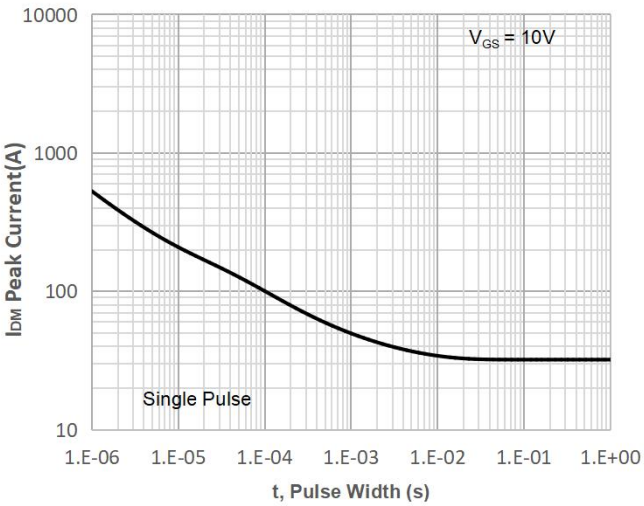


Figure 12: Peak Current Capacity



Test Circuit

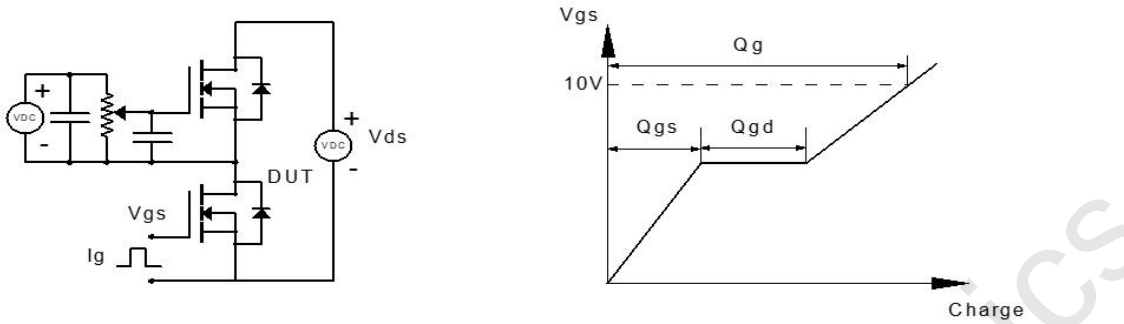


Figure 1: Gate Charge Test Circuit & Waveform

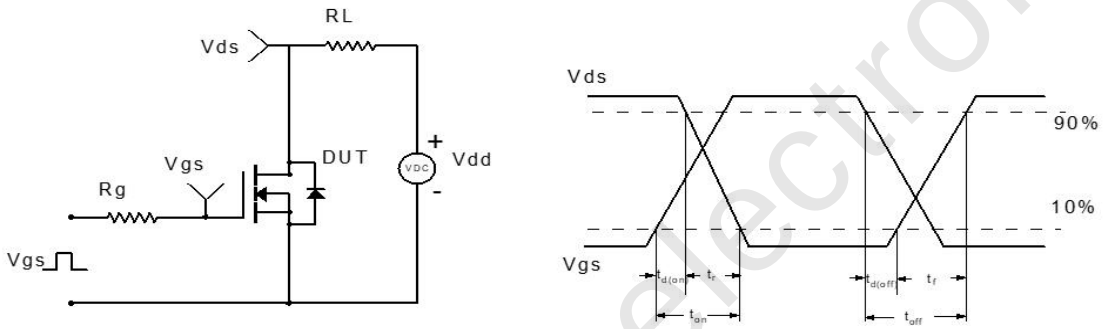


Figure 2: Resistive Switching Test Circuit & Waveform

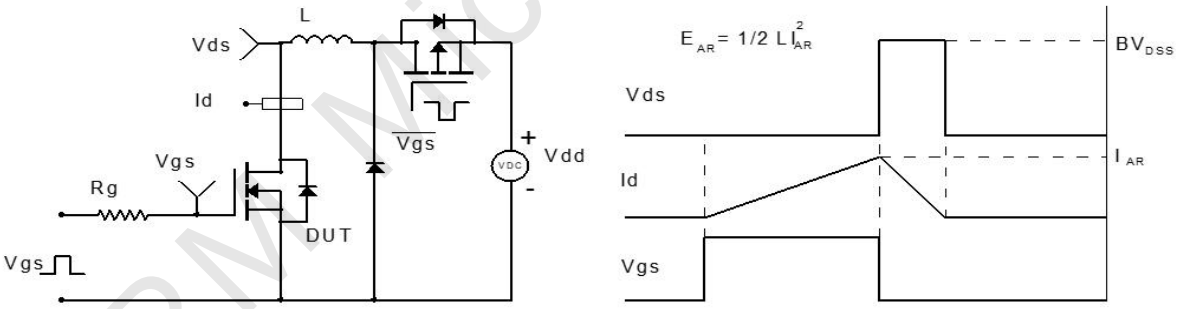


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

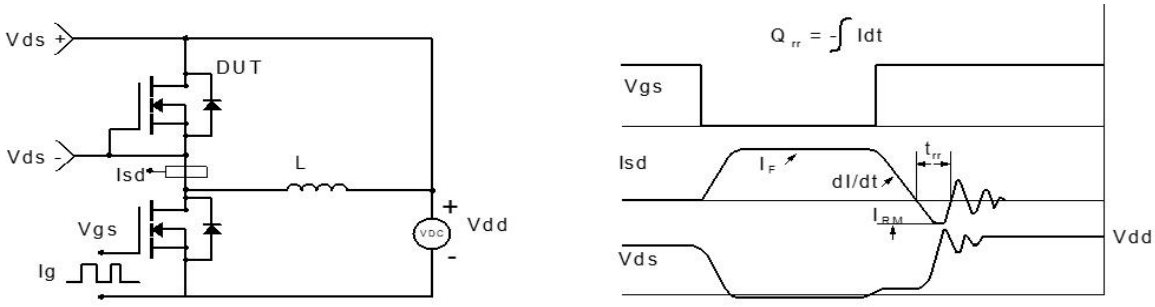
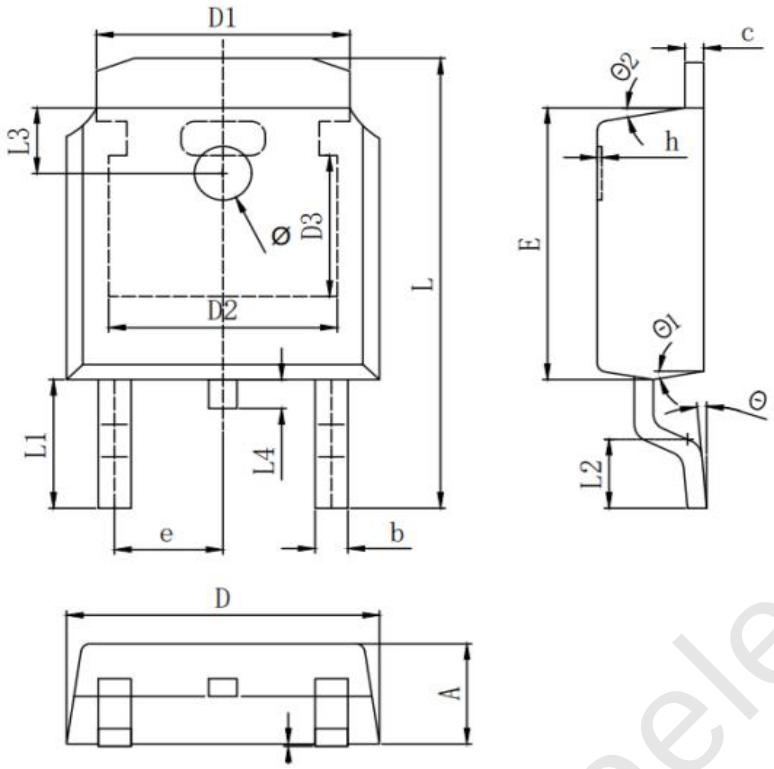


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-252-3L)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

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